



SLLSE40A – SEPTEMBER 2010 – REVISED SEPTEMBER 2011

HIGH-SPEED QUAD DIGITAL ISOLATORS

Check for Samples: ISO7240CF-Q1, ISO7241C-Q1

FEATURES

- Qualified for Automotive Applications
- Selectable Failsafe Output (ISO7240CF)
- 25 and 150-Mbps Signaling Rate Options
 - Low Channel-to-Channel Output Skew;
 1 ns Max
 - Low Pulse-Width Distortion (PWD);2 ns Max
 - Low Jitter Content; 1 ns Typ at 150 Mbps
- Typical 25-Year Life at Rated Working Voltage (see application note SLLA197 and Figure 17)
- 4000-V_{peak} Isolation, 560-V_{peak} V_{IORM}
 - UL 1577, IEC 60747-5-2 (VDE 0884, Rev 2), IEC 61010-1, IEC 60950-1 and CSA Approved

- 4 kV ESD Protection
- Operate With 3.3-V or 5-V Supplies
- High Electromagnetic Immunity (see application report SLLA181)
- -40°C to 125°C Operating Range

DESCRIPTION

The ISO7240, ISO7241 and ISO7242 are quad-channel digital isolators with multiple channel configurations and output enable functions. These devices have logic input and output buffers separated by Tl's silicon dioxide (SiO₂) isolation barrier. Used in conjunction with isolated power supplies, these devices block high voltage, isolate grounds, and prevent noise currents from entering the local ground and interfering with or damaging sensitive circuitry.

The ISO7240 has all four channels in the same direction while the ISO7241 has three channels the same direction and one channel in opposition. The ISO7242 has two channels in each direction.

The C option devices have TTL input thresholds and a noise-filter at the input that prevents transient pulses from being passed to the output of the device. The M option devices have CMOS $V_{CC}/2$ input thresholds and do not have the input noise-filter or the additional propagation delay.

The ISO7240CF has an input disable function on pin 7, and a selectable high or low failsafe-output function with the CTRL pin (pin 10). The failsafe-output is a logic high when a logic-high is placed on the CTRL pin or it is left unconnected. If a logic-low signal is applied to the CTRL pin, the failsafe-output becomes a logic-low output state. The ISO7240CF input disable function prevents data from being passed across the isolation barrier to the output. When the inputs are disabled, the outputs are set by the CTRL pin.

These devices may be powered from either 3.3-V or 5-V supplies on either side in any 3.3-V / 3.3-V, 5-V / 5-V, 5-V / 3.3-V, or 3.3-V / 5-V combination. Note that the signal input pins are 5-V tolerant regardless of the voltage supply level being used.

These devices are characterized for operation over the ambient temperature range of -40°C to 125°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ORDERING INFORMATION⁽¹⁾

T _A	PACKAGE ⁽²⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 125°C		Reel of 2000	ISO7240CFQDWRQ1	ISO7240CFQ
	COIC DW		ISO7240CQDWRQ1	Product Preview
	SOIC – DW		ISO7241CQDWRQ1	ISO7241CQ
			ISO7242CQDWRQ1	ISO7242CQ

- (1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
- (2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

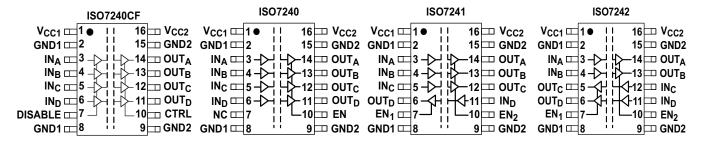


Table 1. ISO724xC Function Table (1)

INPUT V _{CC}	OUTPUT V _{CC}	INPUT (IN)	OUTPUT ENABLE (EN)	OUTPUT (OUT)
		Н	H or Open	Н
DU	PU	L	H or Open	L
PU		X	L	Z
		Open	H or Open	Н
PD	PU	Х	H or Open	Н
PD	PU	X	L	Z

(1) PU = Powered Up; PD = Powered Down; X = Irrelevant; H = High Level; L = Low Level

Table 2. ISO7240CF Function Table

V _{CC1}	V _{CC2}	DATA INPUT (IN)	DISABLE INPUT (DISABLE)	FAILSAFE CONTROL INPUT (CTRL)	DATA OUTPUT (OUT)
PU	PU	Н	L or Open	X	Н
PU	PU	L	L or Open	X	L
Х	PU	X	Н	H or Open	Н
Х	PU	X	Н	L	L
PD	PU	X	Х	H or Open	Н
PD	PU	X	X	L	L

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ABSOLUTE MAXIMUM RATINGS(1)

				VALUE	UNIT
V_{CC}	V _{CC} Supply voltage ⁽²⁾ , V _{CC1} , V _{CC2}				V
V_{I}	V _I Voltage at IN, OUT, EN, DISABLE, CTRL		–0.5 to 6	V	
Io	I _O Output current		±15	mA	
		Human-Body Model		±4	1.37
ESD	Electrostatic discharge	Field-Induced-Charged Device Model	All pins	±1	kV
	alsonarge	Machine Model		±200	V
T _J Maximum junction temperature				150	°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

		MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage (1), V _{CC1} , V _{CC2}	3.15		5.5	V
I _{OH}	High-level output current			4	mA
I _{OL}	Low-level output current	-4			mA
t _{ui}	Input pulse width	40			ns
1/t _{ui}	Signaling rate	0	30 ⁽²⁾	25	Mbps
V_{IH}	High-level input voltage (IN, DISABLE, CTRL, EN)	2		V _{CC}	V
V_{IL}	Low-level input voltage (IN, DISABLE, CTRL, EN)	0		0.8	V
T _A	Operating free-air temperature	-40		125	°C
Н	External magnetic field-strength immunity per IEC 61000-4-8 and IEC 61000-4-9 certification			1000	A/m

For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V. Typical value at room temperature and well-regulated power supply.

IEC 60747-5-2 INSULATION CHARACTERISTICS(1)

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	SPECIFICATIONS	UNIT
V_{IORM}	Maximum working insulation voltage		560	V
		After Input/Output Safety Test Subgroup 2/3 V _{PR} = V _{IORM} × 1.2, t = 10 s, Partial discharge < 5 pC	672	V
V _{PR}	Input to output test voltage	Method a, $V_{PR} = V_{IORM} \times 1.6$, Type and sample test with t = 10 s, Partial discharge < 5 pC	896	V
		Method b1, $V_{PR} = V_{IORM} \times 1.875$, 100 % Production test with t = 1 s, Partial discharge < 5 pC	1050	\
V_{IOTM}	Transient overvoltage	t = 60 s	4000	V
R _S	Insulation resistance	$V_{IO} = 500 \text{ V at T}_{S}$	>10 ⁹	Ω
	Pollution degree		2	

Climatic Classification 40/125/21

All voltage values are with respect to network ground terminal and are peak voltage values.



ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 5-V $^{(1)}$ OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT	
SUPPLY	Y CURRENT							
	10070400	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		1	3	A	
	ISO7240C	25 Mbps	EN ₂ at 3 V		7	10.5	mA	
	ISO7241C	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		6.5	11	A	
I _{CC1}		25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		12	18	mA	
	ISO7242C	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		10	16	A	
		25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		15	24	mA	
	10070400	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		15	22	A	
	ISO7240C	25 Mbps	EN ₂ at 3 V		17	25	mA	
I _{CC2}	ISO7241C	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		13	20	mA	
		25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		18	28	mA	
	ISO7242C	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		10	16	mA	
		25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		15	24	ША	
ELECT	RICAL CHARACTERISTICS							
I _{OFF}	Sleep mode output curre	nt	EN at 0 V, Single channel		0		μΑ	
V	High-level output voltage		I _{OH} = -4 mA, See Figure 1	$V_{CC} - 0.8$			V	
V _{OH}	nigri-ievei output voitage		$I_{OH} = -20 \mu A$, See Figure 1	$V_{CC} - 0.1$			V	
\/	Low lovel output voltage		I _{OL} = 4 mA, See Figure 1			0.4	V	
V_{OL}	Low-level output voltage		I _{OL} = 20 μA, See Figure 1			0.1	V	
V _{I(HYS)}	Input voltage hysteresis				150		mV	
I _{IH}	High-level input current		INI from O \/ to \/			10		
I _{IL}	Low-level input current		IN from 0 V to V _{CC}	-10			μA	
Cı	Input capacitance to grou	ınd	IN at V _{CC} , V _I = 0.4 sin (4E6πt)		2		pF	
CMTI	Common-mode transient	immunity	V _I = V _{CC} or 0 V, See Figure 5	25	50		kV/μs	

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.



SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 5-V OPERATION

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t _{PLH} , t _{PHL}	Propagation delay	Con Figure 4	18	18 45			
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	See Figure 1			5	ns	
t _{sk(pp)}	Part-to-part skew (2)				8	ns	
	Channel to show all output allow (3)	ISO7240C, ISO7241C			3		
0.1(0)	Channel-to-channel output skew (3)	ISO7242C		4		ns	
t _r	Output signal rise time	Con Figure 4		2			
t _f	Output signal fall time	See Figure 1		2		ns	
t _{PHZ}	Propagation delay, high-level-to-high-impedance output			15	25		
t _{PZH}	Propagation delay, high-impedance-to-high-level output	0.0 5 5 00000 0		15	25		
t _{PLZ}	Propagation delay, low-level-to-high-impedance output	See Figure 2		15	25	ns	
t _{PZL}	Propagation delay, high-impedance-to-low-level output			15	25	j	
t _{fs}	Failsafe output delay time from input power loss	See Figure 3		12		μs	
t _{wake}	Wake time from input disable	See Figure 4		15		μs	

Also referred to as pulse skew.

 $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices (2)operate with the same supply voltages, at the same temperature, and have identical packages and test circuits. $t_{sk(o)}$ is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the

same direction while driving identical specified loads.



ELECTRICAL CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V⁽¹⁾ OPERATION

	PARAME1	ΓER	TEST CONDIT	IONS	MIN	TYP	MAX	UNIT
SUPPL	Y CURRENT		1		1			
	ISO7240C	Quiescent	\/ \/ \	aland EN at 2.1/		1	3	A
	1507240C	25 Mbps	$V_I = V_{CC}$ or 0 V, All channels, no load, EN ₂ at 3 V			7	10.5	mA
	ISO7241C	Quiescent	$V_1 = V_{CC}$ or 0 V, All channels, no load, EN ₁ at 3 V, EN ₂ at 3 V			6.5	11	
CC1	15072410	25 Mbps				12	18	mA
	ISO7242C	Quiescent	V _I = V _{CC} or 0 V, All channels, n	o load, EN₁ at 3 V,		10	16	^
	13072420	25 Mbps	EN ₂ at 3 V	·		15	24	mA
	ISO7240C	Quiescent	V - V or 0 V All channels in	a load EN at 2 V		9.5	15	m۸
	15072400	25 Mbps	$V_I = V_{CC}$ or 0 V, All channels, no load, EN ₂ at 3 V			10.5	17	mA
	ISO7241C	Quiescent	$V_1 = V_{CC}$ or 0 V, All channels, no load, EN ₁ at 3 V, EN ₂ at 3 V			8	13	mA
I _{CC2}	13072410	25 Mbps				11.5	18	
	ISO7242C	Quiescent	$V_I = V_{CC}$ or 0 V, All channels, n		6	10	mA	
13072420		25 Mbps	EN ₂ at 3 V		9	14	ША	
ELECT	RICAL CHARACT	TERISTICS						
I _{OFF}	Sleep mode out	put current	EN at 0 V, Single channel			0		μΑ
				ISO7240	V _{CC} - 0.4			
V_{OH}	High-level outpu	tput voltage $I_{OH} = -4 \text{ mA}$, See Figure 1 ISO7 side)		ISO724x (5-V side)	V _{CC} - 0.8			V
			$I_{OH} = -20 \mu A$, See Figure 1		V _{CC} - 0.1			
\/	Low-level outpu	t voltogo	I _{OL} = 4 mA, See Figure 1				0.4	V
V _{OL}	Low-level outpu	t voltage	I_{OL} = 20 μ A, See Figure 1				0.1	V
V _{I(HYS)}	Input voltage hy	steresis				150		mV
l _{IH}	High-level input	current	IN from 0 V to V				10	
I _{IL}	Low-level input	current	IN from 0 V to V _{CC}		-10			μA
Cı	Input capacitano	ce to ground	IN at V_{CC} , $V_{I} = 0.4 \sin (4E6\pi t)$			2		рF
CMTI	Common-mode immunity	transient	V _I = V _{CC} or 0 V, See Figure 5		25	50		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.



SWITCHING CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V OPERATION

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
t _{PLH} , t _{PHL}	Propagation delay	See Figure 1	20		50		
DWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	ISO7240C, ISO7241C			3	ns	
PWD		ISO7242C			4		
t _{sk(pp)}	Part-to-part skew (2)				10	ns	
	Observation about a law (3)	ISO7240C, ISO7241C	3				
t _{sk(o)}	Channel-to-channel output skew (3)	ISO7242C			4	ns	
t _r	Output signal rise time	On a Figure 4		2			
t _f	Output signal fall time	See Figure 1		2		ns	
t _{PHZ}	Propagation delay, high-level-to-high-impedance output			15	25		
t _{PZH}	Propagation delay, high-impedance-to-high-level output	Con Figure 0		15	25		
t _{PLZ}	Propagation delay, low-level-to-high-impedance output	See Figure 2		15	25	ns	
t _{PZL}	Propagation delay, high-impedance-to-low-level output			15	25		
t _{fs}	Failsafe output delay time from input power loss	See Figure 3		18		μs	
t _{wake}	Wake time from input disable	See Figure 4		15		μs	

⁽¹⁾ Also known as pulse skew

⁽²⁾ t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

⁽³⁾ $t_{sk(0)}$ is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.



ELECTRICAL CHARACTERISTICS: V_{CC1} at 3.3-V, V_{CC2} at 5-V⁽¹⁾ OPERATION

	PARAMETE	R	TEST CONDI	TIONS	MIN	TYP	MAX	UNIT	
SUPPLY	CURRENT						,		
	10070400	Quiescent	V _I = V _{CC} or 0 V, All channels,	no load, EN ₂ at 3 V		0.5	1	Δ	
	ISO7240C	25 Mbps				3	5	mA	
	ISO7241C	Quiescent	$V_1 = V_{CC}$ or 0 V, All channels, EN_2 at 3 V	no load, EN ₁ at 3 V,		4	7	mA	
I _{CC1}		25 Mbps					11		
	ISO7242C	Quiescent	$V_1 = V_{CC}$ or 0 V, All channels, EN_2 at 3 V	no load, EN ₁ at 3 V,		6	10	mA	
		25 Mbps				9	14		
	10070400	Quiescent	V _I = V _{CC} or 0 V, All channels,	no load, EN ₂ at 3 V		15	22		
	ISO7240C	25 Mbps				17	25	mA	
	ISO7241C	Quiescent	$\rm V_{\rm I} = \rm V_{\rm CC}$ or 0 V, All channels, no load, $\rm EN_{\rm 1}$ at 3 V, $\rm EN_{\rm 2}$ at 3 V			13	20	mA	
I_{CC2}		25 Mbps				18	28		
	ISO7242C	Quiescent	$V_1 = V_{CC}$ or 0 V, All channels, EN_2 at 3 V	V_{I} = V_{CC} or 0 V, All channels, no load, EN $_{\text{1}}$ at 3 V, EN $_{\text{2}}$ at 3 V		10	16	mA	
	25 Mbps				15	24			
ELECTE	RICAL CHARACTE	RISTICS					,		
I _{OFF}	Sleep mode outp	out current	EN at 0 V, Single channel			0		μΑ	
			1 AmA Con Figure 1	ISO7240	V _{CC} - 0.4				
V_{OH}	High-level outpu	t voltage	I _{OH} = –4 mA, See Figure 1	ISO724x (5-V side)	$V_{CC} - 0.8$		V		
			$I_{OH} = -20 \mu A$, See Figure 1		V _{CC} - 0.1				
V	Low lovel output	voltogo	I _{OL} = 4 mA, See Figure 1				0.4	V	
V_{OL}	Low-level output	voltage	I_{OL} = 20 μ A, See Figure 1				0.1	V	
$V_{I(HYS)}$	Input voltage hys	steresis				150		mV	
I _{IH}	High-level input	h-level input current u-level input current IN from 0 V to V _{CC}				10			
I _{IL}	Low-level input of			-10			μA		
Cı	Input capacitanc	e to ground	IN at V_{CC} , $V_I = 0.4 \sin (4E6\pi t)$)		2		pF	
CMTI	Common-mode immunity	ransient	V _I = V _{CC} or 0 V, See Figure 5		25	50		kV/μs	

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.



SWITCHING CHARACTERISTICS: V_{CC1} at 3.3-V and V_{CC2} at 5-V OPERATION

	PARAMETER	TEST CONDITIONS		MIN	TYP	MA X	UNIT
t _{PLH} , t _{PHL}	Propagation delay	See Figure 1		20		51	
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	See Figure 1	ISO7240C, ISO7241C			3	ns
			ISO7242C			4	
t _{sk(pp)}	Part-to-part skew (2)					10	ns
	Character sharped systems also (3)	ISO7240C, ISO72410	С			3	
t _{sk(o)}	Channel-to-channel output skew (3)	ISO7242C				4	ns
t _r	Output signal rise time	Con Figure 4			2		
t _f	Output signal fall time	See Figure 1			2		ns
t _{PHZ}	Propagation delay, high-level-to-high-impedance output				15	25	
t _{PZH}	Propagation delay, high-impedance-to-high-level output	Coo Figure 0			15	25	
t _{PLZ}	Propagation delay, low-level-to-high-impedance output	See Figure 2			15	25	ns
t _{PZL}	Propagation delay, high-impedance-to-low-level output				15	25	
t _{fs}	Failsafe output delay time from input power loss	See Figure 3			12		μs
t _{wake}	Wake time from input disable	See Figure 4			15		μs

⁽¹⁾ Also known as pulse skew

⁽²⁾ t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

⁽³⁾ t_{sk(o)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.



ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3 $V^{(1)}$ OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT					'!	
	10070400	Quiescent	$V_{I} = V_{CC}$ or 0 V, all channels, no load,		0.5	1	A
	ISO7240C	25 Mbps	EN ₂ at 3 V		3	5	mA
	ISO7241C	Quiescent	V _I = V _{CC} or 0 V, all channels, no load,		4	7	
I _{CC1}		25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		6.5	11	A
	ISO7242C	Quiescent	$V_I = V_{CC}$ or 0 V, all channels, no load,		6	10	mA
		25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		9	14	
	10070400	Quiescent	$V_I = V_{CC}$ or 0 V, all channels, no load,		9.5	15	A
	ISO7240C	25 Mbps	EN ₂ at 3 V		10.5	17	mA
	ISO7241C	Quiescent	$V_I = V_{CC}$ or 0 V, all channels, no load,		8	13	<u> </u>
I _{CC2}		25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		11.5	18	A
	ISO7242C	Quiescent	$V_I = V_{CC}$ or 0 V, all channels, no load,		6	10	mA
		25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V	9		14	
ELECTR	RICAL CHARACTERISTICS						
I _{OFF}	Sleep mode output current		EN at 0 V, single channel		0		μΑ
V	Lligh lovel output voltage		I _{OH} = -4 mA, See Figure 1	V _{CC} - 0.4			V
V _{OH}	High-level output voltage		$I_{OH} = -20 \mu A$, See Figure 1	V _{CC} - 0.1			V
\/	Lave lavel avitavit valtage		I _{OL} = 4 mA, See Figure 1			0.4	V
V_{OL}	Low-level output voltage		I _{OL} = 20 μA, See Figure 1				V
V _{I(HYS)}	Input voltage hysteresis				150		mV
I _{IH}	High-level input current Low-level input current		INI frame O.V. an V.			10	
I _{IL}			IN from 0 V or V _{CC}	-10			μA
Cı	Input capacitance to ground	I	IN at V_{CC} , $V_I = 0.4 \sin (4E6\pi t)$		2		pF
CMTI	Common-mode transient immunity		V _I = V _{CC} or 0 V, See Figure 5	25	50		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.



SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3-V OPERATION

	PARAMETER	TEST	MI N	TY P	MAX	UNIT	
t _{PLH} , t _{PHL}	Propagation delay	See Figure 1	25		56	ns	
PWD	Pulse-width distortion $ t_{PHL} - t_{PLH} ^{(1)}$					4	
t _{sk(pp)}	Part-to-part skew (2)					10	ns
	Channel-to-channel output skew (3)	ISO7240C, ISO7241C				3.5	
t _{sk(o)}	Channel-to-channel output skew	ISO7242C			4	ns	
t _r	Output signal rise time	Coo Figure 4			2		ns
t _f	Output signal fall time	See Figure 1			2		ns
t _{PHZ}	Propagation delay, high-level-to-high-impedance output		ISO7240C, ISO7241C		15	20	
			ISO7242C		15	25	
t _{PZH}	Propagation delay, high-impedance-to-high-level output		ISO7240C, ISO7241C		15	20	
		0 5 0	ISO7242C		15	25	
t _{PLZ}	Propagation delay, low-level-to-high-impedance output	See Figure 2	ISO7240C, ISO7241C		15	20	ns
			ISO7242C		15	25	
t _{PZL}	Propagation delay, high-impedance-to-low-level output		ISO7240C, ISO7241C		15	5 20	
			ISO7242C		15	25	
t _{fs}	Failsafe output delay time from input power loss	See Figure 3	,		18		μs
t _{wake}	Wake time from input disable	See Figure 4			15		μs

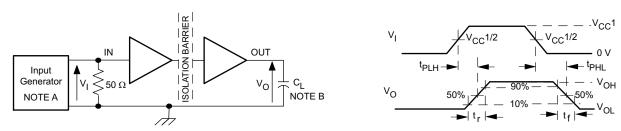
⁽¹⁾ Also referred to as pulse skew.

⁽²⁾ t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

⁽³⁾ $t_{sk(o)}$ is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.

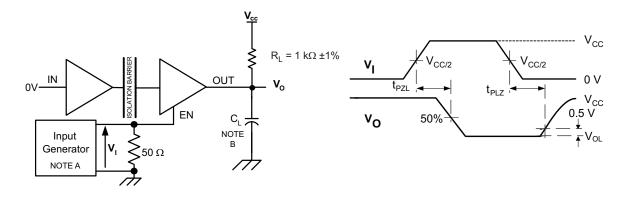


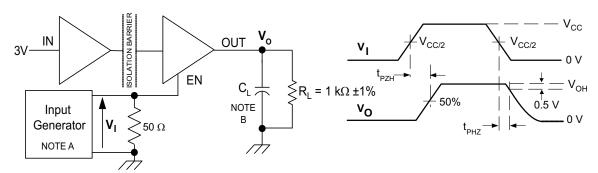
PARAMETER MEASUREMENT INFORMATION



- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50\Omega$.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 1. Switching Characteristic Test Circuit and Voltage Waveforms



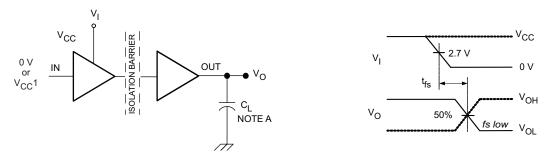


- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50\Omega$.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 2. Enable/Disable Propagation Delay Time Test Circuit and Waveform

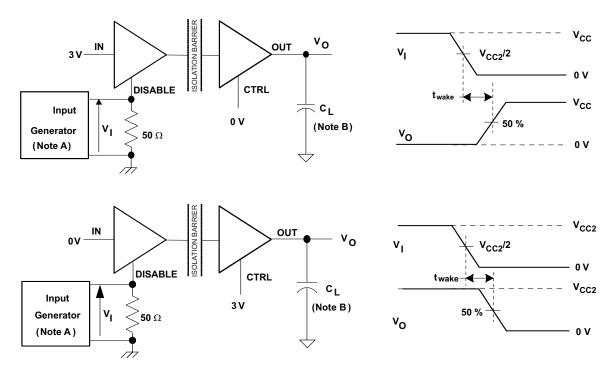


PARAMETER MEASUREMENT INFORMATION (continued)



- A. C_L = 15 pF and includes instrumentation and fixture capacitance within ±20%.
- B. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50\Omega$.

Figure 3. Failsafe Delay Time Test Circuit and Voltage Waveforms



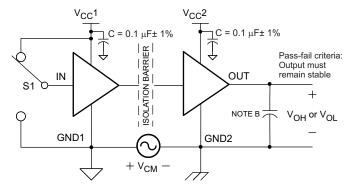
NOTE: Which ever test yields the longest time is used in this data sheet

A. Whichever test yields the longest time is used in this data sheet.

Figure 4. Wake Time From Input Disable Test Circuit and Voltage Waveforms

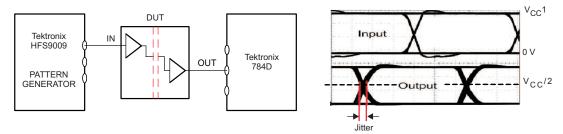


PARAMETER MEASUREMENT INFORMATION (continued)



- A. $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.
- B. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50\Omega$.

Figure 5. Common-Mode Transient Immunity Test Circuit and Voltage Waveform



NOTE: PRBS bit pattern run length is 2¹⁶ – 1. Transition time is 800 ps. NRZ data input has no more than five consecutive 1s or 0s.

Figure 6. Peak-to-Peak Eye-Pattern Jitter Test Circuit and Voltage Waveform



DEVICE INFORMATION

PACKAGE CHARACTERISTICS

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (Clearance)	Shortest terminal-to-terminal distance through air	8.34			mm
L(102)	Minimum external tracking (Creepage)	Shortest terminal-to-terminal distance across the package surface	8.1			mm
C _{TI}	Tracking resistance (comparative tracking index)	DIN IEC 60112/VDE 0303 Part 1	≥ 175			V
	Minimum Internal Gap (Internal Clearance)	Distance through the insulation	0.008			mm
R _{IO}	Isolation resistance	Input to output, V_{IO} = 500 V, all pins on each side of the barrier tied together creating a two-terminal device		>10 ¹²		Ω
C _{IO}	Barrier capacitance Input to output	V _I = 0.4 sin (4E6πt)		2		pF
Cı	Input capacitance to ground	V _I = 0.4 sin (4E6πt)		2		pF

IEC 60664-1 RATINGS TABLE

PARAMETER	TEST CONDITIONS	SPECIFICATION
Basic isolation group	Material group	Illa
Installation algorification	Rated mains voltage ≤150 VRMS	I-IV
Installation classification	Rated mains voltage ≤300 VRMS	1-111

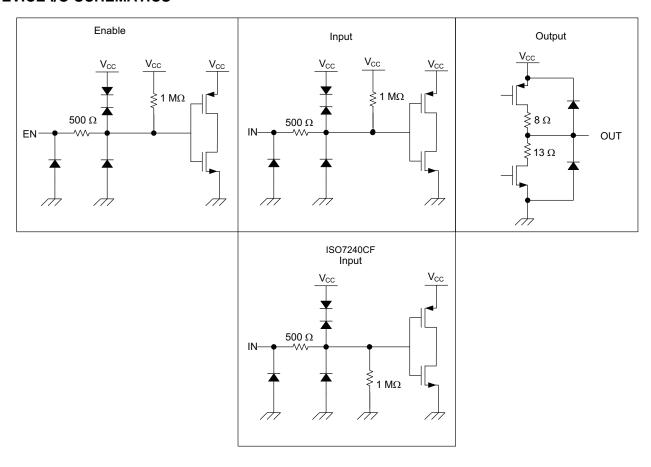
REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2	Approved under CSA Component Acceptance Notice	Recognized under 1577 Component Recognition Program ⁽¹⁾
File Number: 40016131	File Number: 1698195	File Number: E181974

(1) Production tested ≥ 3000 Vrms for 1 second in accordance with UL 1577.



DEVICE I/O SCHEMATICS



THERMAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	PARAMETER TEST CONDITIONS				UNIT
0	lunction to air	Low-K Thermal Resistance ⁽¹⁾		168		°C/W
θ_{JA}	Junction-to-air	High-K Thermal Resistance		96.1		C/VV
θ_{JB}	Junction-to-Board Thermal Resistance			61		°C/W
θ_{JC}	Junction-to-Case Thermal Resistance			48		°C/W
P_D	Device Power Dissipation	$V_{CC1} = V_{CC2} = 5.5 \text{ V}, T_J = 150^{\circ}\text{C}, C_L = 15 \text{ pF},$ Input a 50% duty cycle square wave			220	mW

(1) Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages.



TYPICAL CHARACTERISTIC CURVES

ISO7240C RMS SUPPLY CURRENT

SIGNALING RATE 45 T_A = 25°C, Load = 15 pF, 40 All Channels 35 I_{CC} - Supply Current - mA/RMS 5-V I_{CC2} 30 3.3-V I_{CC2} 25 20 15 10 5 - 3.3-V I_{CC1} 0 75 100 125 Signaling Rate - Mbps

Figure 7.

ISO7241C RMS SUPPLY CURRENT

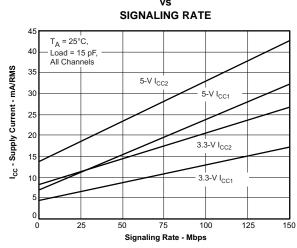
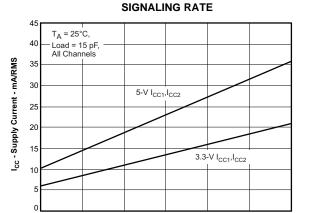


Figure 8.

ISO7242C RMS SUPPLY CURRENT



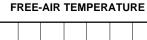
Signaling Rate - Mbps Figure 9.

100

125

150

PROPAGATION DELAY



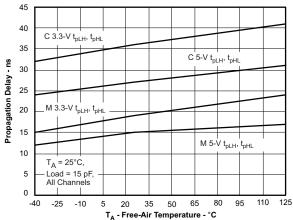


Figure 10.

25



TYPICAL CHARACTERISTIC CURVES (continued)

INPUT VOLTAGE THRESHOLD

FREE-AIR TEMPERATURE

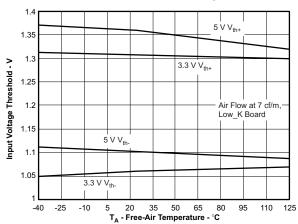
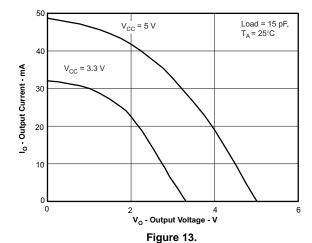


Figure 11.

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HIGH-LEVEL OUTPUT CURRENT vs HIGH-LEVEL OUTPUT VOLTAGE



V_{CC1} FAILSAFE THRESHOLD vs

FREE-AIR TEMPERATURE

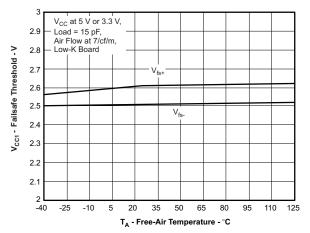


Figure 12.

LOW-LEVEL OUTPUT CURRENT vs LOW-LEVEL OUTPUT VOLTAGE

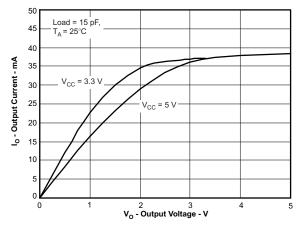


Figure 14.



APPLICATION INFORMATION

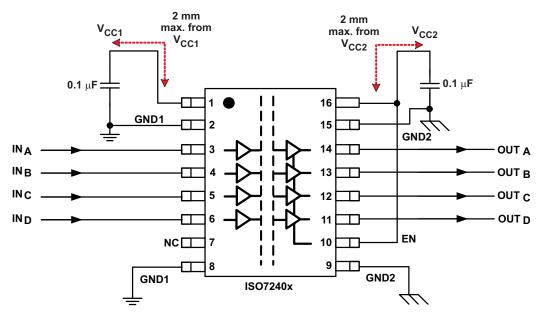


Figure 15. Typical ISO7240x Application Circuit

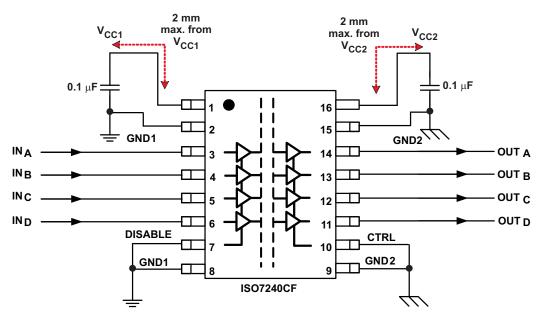


Figure 16. Typical ISO7240CF Failsafe-Low Application Circuit

LIFE EXPECTANCY vs WORKING VOLTAGE

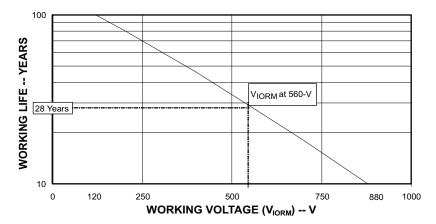


Figure 17. Time-Dependant Dielectric Breakdown Testing Results



PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
ISO7240CFQDWRQ1	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7240CFQ	Samples
ISO7241CQDWRQ1	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7241CQ	Samples
ISO7242CQDWRQ1	ACTIVE	SOIC	DW	16	2000	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 125	ISO7242CQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF ISO7240CF-Q1, ISO7241C-Q1, ISO7242C-Q1:

• Catalog: ISO7240CF, ISO7241C, ISO7242C

NOTE: Qualified Version Definitions:

Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com 26-Feb-2019

TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

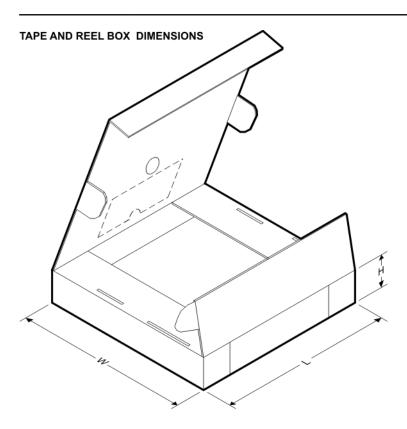
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7240CFQDWRQ1	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7241CQDWRQ1	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7242CQDWRQ1	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

www.ti.com 26-Feb-2019



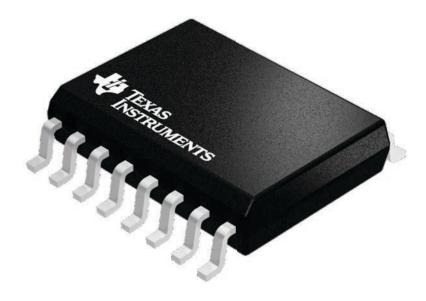
*All dimensions are nominal

7 til dillionolorio aro nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7240CFQDWRQ1	SOIC	DW	16	2000	350.0	350.0	43.0
ISO7241CQDWRQ1	SOIC	DW	16	2000	350.0	350.0	43.0
ISO7242CQDWRQ1	SOIC	DW	16	2000	350.0	350.0	43.0

7.5 x 10.3, 1.27 mm pitch

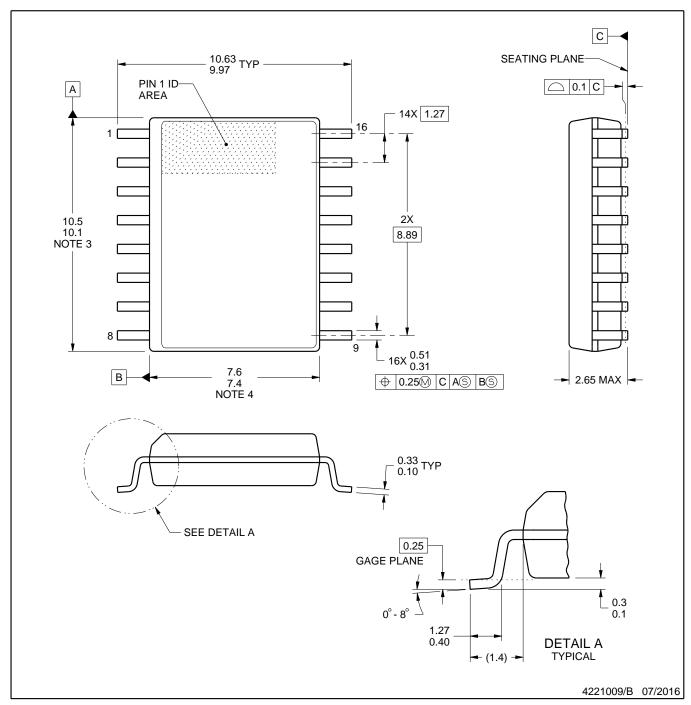
SMALL OUTLINE INTEGRATED CIRCUIT

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





SOIC



NOTES:

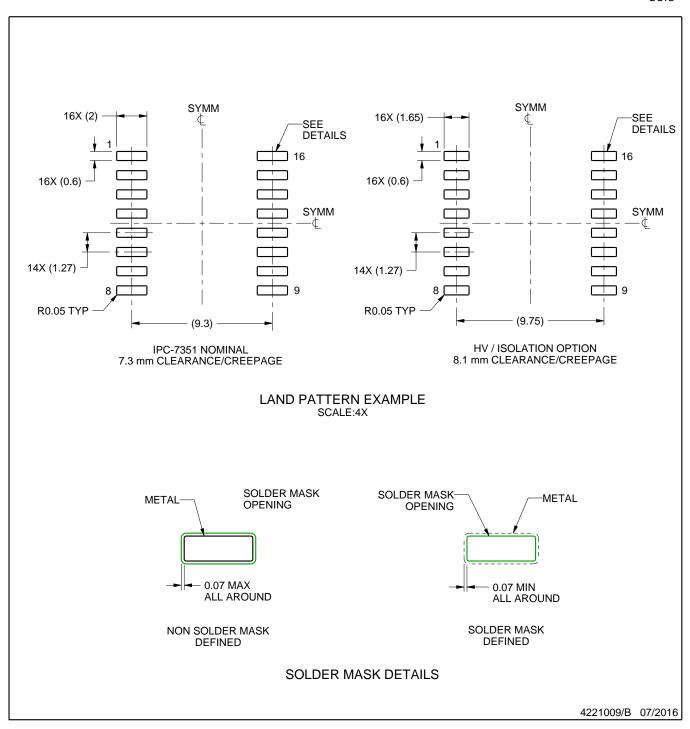
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing
- per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm, per side.
- 5. Reference JEDEC registration MS-013.



SOIC



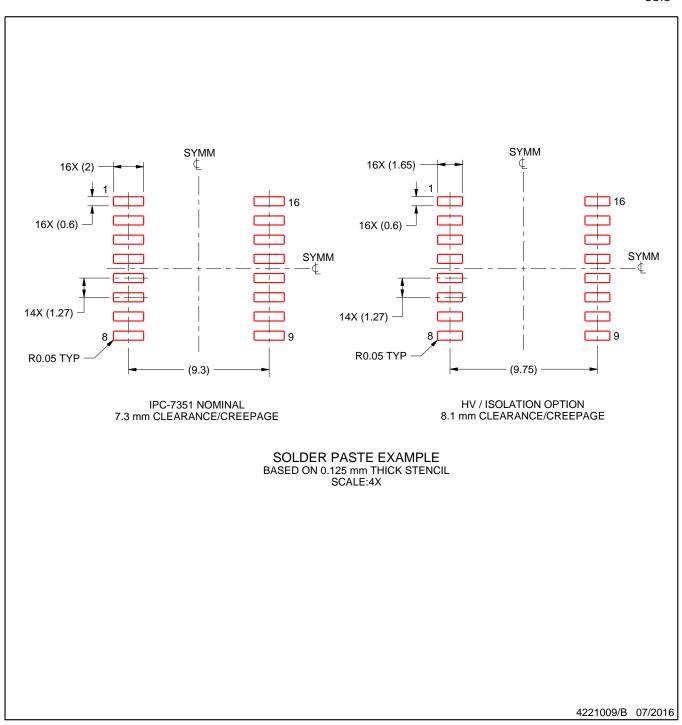
NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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